

Search History (16 pp.) 8/17/05

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|---|------------------|---------|------------------|
| L2 | 5 | "773333".ap. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/17 12:18 |
| L3 | 1 | (low-voltage "low" adj voltage) and (tft thin adj film adj transistor) and (self-align\$3 self-aligned self-alignment selfalign\$3 selfalignment) and overlap near4 ("mu.m" micron ">ANG." Angstrom Angstroem) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/17 12:20 |
| L4 | 1 | (low-voltage "low" adj voltage) and (tft thin adj film adj transistor) and (self-align\$3 self-aligned self-alignment selfalign\$3 selfalignment) and overlap near4 ("mu.m" micron "ANG." Angstrom Angstroem) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/17 12:21 |
| L5 | 1 | (low-voltage "low" adj voltage) and (tft thin adj film adj transistor) and (self-align\$3 self-aligned self-alignment selfalign\$3 selfalignment) and (overlapping overlapped overlap) near4 ("mu.m" micron "ANG." Angstrom Angstroem) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/17 12:22 |
| L6 | 14 | (tft thin adj film adj transistor) and (self-align\$3 self-aligned self-alignment selfalign\$3 selfalignment) and (overlapping overlapped overlap) near4 ("mu.m" micron "ANG." Angstrom Angstroem) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/17 12:59 |
| L7 | 2219 | (self-alignment self-align\$3 selfalign\$3 selfalignment).ti,ab, clm. and (LDD lightly adj doped adj drain lightly-doped adj dran) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/17 13:00 |
| L8 | 2219 | (self-alignment self-align\$3 selfalign\$3 selfalignment).ti,ab, clm. and (LDD lightly adj doped adj drain lightly-doped adj drain) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/17 13:00 |
| L9 | 1012 | (self-alignment self-align\$3 selfalign\$3 selfalignment).ti,ab, clm. and (LDD lightly adj doped adj drain lightly-doped adj drain). ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/17 13:00 |

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| L10 | 136 | (self-alignment self-align\$3 selfalign\$3 selfalignment).ti,ab, clm. and (LDD lightly adj doped adj drain lightly-doped adj drain). ti,ab,clm. and (thin adj film adj transistor tft otft).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/17 13:05 |
| L11 | 5 | (self-alignment self-align\$3 selfalign\$3 selfalignment).ti,ab, clm. and (LDD lightly adj doped adj drain lightly-doped adj drain). ti,ab,clm. and (thin adj film adj transistor tft otft).ti,ab,clm. and hot adj electron adj effect | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/17 13:05 |
| L12 | 9 | (self-alignment self-align\$3 selfalign\$3 selfalignment).ti,ab, clm. and (LDD lightly adj doped adj drain lightly-doped adj drain). ti,ab,clm. and (thin adj film adj transistor tft otft).ti,ab,clm. and hot adj electron | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/17 13:05 |
| S1 | 2 | jp-05335573\$-.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/16 08:24 |
| S2 | 0 | jp-200345892\$-.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/05 16:37 |
| S3 | 2 | jp-2003045892\$-.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/05 16:37 |
| S4 | 2 | jp-08250742\$-.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/05 16:37 |
| S5 | 2 | jp-11307777\$-.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/05 16:37 |
| S6 | 2 | jp-2000353811\$-.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/05 16:41 |

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| S7 | 10 | S1 S2 S3 S4 S5 S6 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/16 17:11 |
| S8 | 5 | "773333".ap. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/05 16:44 |
| S9 | 18 | (tft thin adj film adj transistor) and overlap near6 ("low" "high") near2 voltage | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/05 17:05 |
| S10 | 4455 | "low" near2 voltage and "high" near2 voltage and (tft thin adj film adj transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/05 17:09 |
| S11 | 80 | "low" near2 voltage near20 gate adj (insulation insulating oxide) and "high" near2 voltage near20 gate adj (insulation insulating oxide) and (tft thin adj film adj transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/05 17:10 |
| S12 | 5683 | ((257/59) or (257/72) or (257/351) or (257/355) or (257/356) or (257/390) or (257/391) or (257/392) or (257/393) or (257/394) or (257/395) or (257/406)).CCLS | US-PGPUB; USPAT | OR | OFF | 2005/03/05 17:39 |
| S13 | 19 | S12 and gate adj insulat\$3.clm. and "high" adj2 voltage.clm. and "low" adj2 voltage.clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/05 17:44 |
| S14 | 133 | (257/406).CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/05 17:44 |

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| S15 | 42 | (US-20040195568-\$ or US-20040046174-\$ or US-20030025127-\$ or US-20020149056-\$ or US-20020135554-\$ or US-20020042170-\$ or US-20020041350-\$ or US-20020030190-\$ or US-20020024048-\$ or US-20010013912-\$ or US-20010000755-\$ or US-20040026750-\$ or US-20020084490-\$).did. or (US-6856360-\$ or US-6657228-\$ or US-6452211-\$ or US-6426787-\$ or US-6420988-\$ or US-6400434-\$ or US-6384886-\$ or US-6368904-\$ or US-6316787-\$ or US-6303963-\$ or US-6294815-\$ or US-6165824-\$ or US-6163055-\$ or US-6115094-\$ or US-5528056-\$ or US-6597046-\$ or US-5468987-\$).did. or (JP-2003045892-\$ or JP-2000353811-\$ or JP-11307777-\$ or JP-08250742-\$ or JP-05335573-\$ or JP-54015678-\$ or JP-02222169-\$).did. or (US-20030025127-\$ or JP-2000353811-\$ or JP-11307777-\$ or JP-08250742-\$ or JP-05335573-\$).did. | US-PGPUB; USPAT; JPO; DERWENT | OR | OFF | 2005/03/05 18:05 |
| S16 | 317 | (257/391).CCLS. | US-PGPUB; USPAT | OR | OFF | 2005/03/05 18:06 |

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| S17 | 46 | (US-20040195568-\$ or US-20040046174-\$ or US-20030025127-\$ or US-20020149056-\$ or US-20020135554-\$ or US-20020042170-\$ or US-20020041350-\$ or US-20020030190-\$ or US-20020024048-\$ or US-20010013912-\$ or US-20010000755-\$ or US-20040026750-\$ or US-20020084490-\$ or US-20020190343-\$ or US-20020117723-\$).did. or (US-6856360-\$ or US-6657228-\$ or US-6452211-\$ or US-6426787-\$ or US-6420988-\$ or US-6400434-\$ or US-6384886-\$ or US-6368904-\$ or US-6316787-\$ or US-6303963-\$ or US-6294815-\$ or US-6165824-\$ or US-6163055-\$ or US-6115094-\$ or US-5528056-\$ or US-6597046-\$ or US-5468987-\$ or US-6541823-\$ or US-5576556-\$).did. or (JP-2003045892-\$ or JP-2000353811-\$ or JP-11307777-\$ or JP-08250742-\$ or JP-05335573-\$ or JP-54015678-\$ or JP-02222169-\$).did. or (US-20030025127-\$ or JP-2000353811-\$ or JP-11307777-\$ or JP-08250742-\$ or JP-05335573-\$).did. | US-PGPUB; USPAT; JPO; DERWENT | OR | OFF | 2005/03/05 18:33 |
| S18 | 5 | S17 and double adj gate | US-PGPUB; USPAT; JPO; DERWENT | OR | OFF | 2005/03/05 18:35 |
| S19 | 2 | S17 and ((additional extra second double) adj gate sub-gate) near5 (withstand break-down breakdown) near2 voltage | US-PGPUB; USPAT; JPO; DERWENT | OR | OFF | 2005/03/05 18:47 |
| S20 | 326 | (257/392).CCLS. | US-PGPUB; USPAT | OR | OFF | 2005/03/05 18:57 |
| S21 | 138 | (257/270).CCLS. | US-PGPUB; USPAT | OR | OFF | 2005/03/05 18:59 |
| S22 | 264 | (257/346).CCLS. | US-PGPUB; USPAT | OR | OFF | 2005/03/05 19:06 |
| S23 | 159 | (257/387).CCLS. | US-PGPUB; USPAT | OR | OFF | 2005/08/16 12:38 |

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| S24 | 5 | "low" near1 voltage near10 (tft thin adj film adj transistor) near10 (self-alignment selfaligned overlap overlapping) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/05 19:14 |
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| S25 | 82 | (US-20040195568-\$ or US-20040046174-\$ or US-20030025127-\$ or US-20020149056-\$ or US-20020135554-\$ or US-20020042170-\$ or US-20020041350-\$ or US-20020030190-\$ or US-20020024048-\$ or US-20010013912-\$ or US-20010000755-\$ or US-20040026750-\$ or US-20020084490-\$ or US-20020190343-\$ or US-20020117723-\$ or US-20030132500-\$).did. or (US-6856360-\$ or US-6657228-\$ or US-6452211-\$ or US-6426787-\$ or US-6420988-\$ or US-6400434-\$ or US-6384886-\$ or US-6368904-\$ or US-6316787-\$ or US-6303963-\$ or US-6294815-\$ or US-6165824-\$ or US-6163055-\$ or US-6115094-\$ or US-5528056-\$ or US-6597046-\$ or US-5468987-\$ or US-6541823-\$ or US-5576556-\$ or US-6847080-\$ or US-6847088-\$ or US-6853030-\$ or US-6770940-\$ or US-6653694-\$ or US-6646313-\$ or US-6627963-\$).did. or (US-6593191-\$ or US-6586805-\$ or US-6579736-\$ or US-6563182-\$ or US-6559489-\$ or US-6492690-\$ or US-6380590-\$ or US-6333541-\$ or US-6300663-\$ or US-6271572-\$ or US-6267479-\$ or US-6265739-\$ or US-6251732-\$ or US-6198140-\$ or US-6191460-\$ or US-6175138-\$ or US-6166417-\$ or US-6093594-\$ or US-5696400-\$ or US-5654577-\$ or US-4205330-\$ or US-4183040-\$ or US-4104784-\$ or US-4085498-\$ or US-6157062-\$ or US-6064096-\$ or US-5736750-\$).did. or (US-6469348-\$).did. or (JP-2003045892-\$ or JP-2000353811-\$ or JP-11307777-\$ or JP-08250742-\$ or JP-05335573-\$ or JP-54015678-\$ or JP-02222169-\$).did. or (US-20030025127-\$ or JP-2000353811-\$ or JP-11307777-\$ or JP-08250742-\$ or JP-05335573-\$).did. | US-PGPUB; USPAT; JPO; DERWENT | OR | OFF | 2005/03/05 19:19 |
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| S26 | 10 | (JP-05335573-\$ or JP-08250742-\$ or JP-11307777-\$ or JP-2000353811-\$ or JP-2003045892-\$).did. or (JP-05335573-\$ or JP-08250742-\$ or JP-11307777-\$ or JP-2000353811-\$ or US-20030025127-\$).did. | JPO; DERWENT | OR | OFF | 2005/03/05 19:43 |
| S27 | 1 | ("6509602").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/05 19:51 |
| S28 | 14 | S25 and (overlap overlapping) near4 (source drain gate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/05 19:52 |
| S29 | 1 | ikeda.in. and yamazaki.in. and thinner.ab. and gate and pixel and TFT.ab. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/05 20:16 |
| S30 | 465 | (overlap overlapping) near10 (self-alignment self-aligned) and gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/05 21:34 |
| S31 | 207 | (overlap overlapping) near4 (self-alignment self-aligned) and gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/05 21:34 |
| S32 | 102 | (overlap overlapping) near4 (self-alignment self-aligned) near4 gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/05 21:35 |
| S33 | 22 | (overlap overlapping) near4 (self-alignment self-aligned) near4 gate and tft | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/05 21:35 |

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| S34 | 82 | (US-20010000755-\$ or US-20010013912-\$ or US-20020024048-\$ or US-20020030190-\$ or US-20020041350-\$ or US-20020042170-\$ or US-20020084490-\$ or US-20020117723-\$ or US-20020135554-\$ or US-20020149056-\$ or US-20020190343-\$ or US-20030025127-\$ or US-20030132500-\$ or US-20040026750-\$ or US-20040046174-\$ or US-20040195568-\$).did. or (US-4085498-\$ or US-4104784-\$ or US-4183040-\$ or US-4205330-\$ or US-5468987-\$ or US-5528056-\$ or US-5576556-\$ or US-5654577-\$ or US-5696400-\$ or US-5736750-\$ or US-6064096-\$ or US-6093594-\$ or US-6115094-\$ or US-6157062-\$ or US-6163055-\$ or US-6165824-\$ or US-6166417-\$ or US-6175138-\$ or US-6191460-\$ or US-6198140-\$ or US-6251732-\$ or US-6265739-\$ or US-6267479-\$ or US-6271572-\$ or US-6294815-\$ or US-6300663-\$).did. or (US-6303963-\$ or US-6316787-\$ or US-6333541-\$ or US-6368904-\$ or US-6380590-\$ or US-6384886-\$ or US-6400434-\$ or US-6420988-\$ or US-6426787-\$ or US-6452211-\$ or US-6469348-\$ or US-6492690-\$ or US-6541823-\$ or US-6559489-\$ or US-6563182-\$ or US-6579736-\$ or US-6586805-\$ or US-6593191-\$ or US-6597046-\$ or US-6627963-\$ or US-6646313-\$ or US-6653694-\$ or US-6657228-\$ or US-6770940-\$ or US-6847080-\$ or US-6847088-\$ or US-6853030-\$).did. or (US-6856360-\$).did. or (JP-02222169-\$ or JP-05335573-\$ or JP-08250742-\$ or JP-11307777-\$ or JP-2000353811-\$ or JP-2003045892-\$ or JP-54015678-\$).did. or (JP-05335573-\$ or JP-08250742-\$ or JP-2000353811-\$ or JP-11307777-\$ or US-20030025127-\$).did. | US-PGPUB; USPAT; JPO; DERWENT | OR | OFF | 2005/03/06 07:33 |
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| S35 | 3 | S34 and yanai.in. | US-PGPUB; USPAT; JPO; DERWENT | OR | OFF | 2005/03/06 07:40 |
| S36 | 28 | (self-aligned self-aligning self-alignment) near10 (" ANG " " mu.m" micron nm nanometer Angstrom) and tft | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/06 07:45 |
| S37 | 22 | (self-aligned self-aligning self-alignment) and LDD and S34 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/06 07:55 |
| S38 | 15 | (self-aligned self-aligning self-alignment) and LDD and "low" near1 voltage and S34 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/06 07:56 |
| S39 | 15 | (self-aligned self-aligning self-alignment) and LDD and "low" near1 voltage and "high" near1 voltage and S34 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/06 08:05 |
| S40 | 126 | LDD near4 "low" near1 voltage | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/06 08:05 |
| S41 | 14 | LDD near4 "low" near1 voltage and tft | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/06 08:36 |
| S42 | 5 | LDD near4 "low" near1 voltage and tft and (self-aligned self-aligning self-alignment selfaligned selfalignment) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/06 08:36 |
| S43 | 238 | second adj electrode near6 TFT | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/06 10:21 |

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| S44 | 19 | split-gate and TFT | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/06 10:27 |
| S45 | 131 | separate near1 gate and TFT | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/06 12:22 |
| S46 | 60 | separate near1 gate and TFT | US-PGPUB | OR | OFF | 2005/03/06 12:25 |
| S47 | 654 | double adj gate and tft | US-PGPUB | OR | OFF | 2005/03/06 12:26 |
| S48 | 15 | double adj gate.ti,ab,clm. and tft | US-PGPUB | OR | OFF | 2005/03/06 12:48 |
| S49 | 2 | (overlap overlapping) near6 gate near6 ("."mu.m" ".ANG." nm nanometer micron) and tft.ti,ab, clm. | US-PGPUB; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/03/06 13:01 |
| S50 | 7 | (overlap overlapping) near6 gate near6 ("."mu.m" ".ANG." nm nanometer micron) and tft | US-PGPUB; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/03/06 13:36 |
| S51 | 83 | (overlap overlapping) near6 ("."mu. m" ".ANG." nm nanometer micron) and tft | US-PGPUB; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/03/06 13:36 |
| S52 | 10 | (JP-2003045892-\$ or JP-2000353811-\$ or JP-05335573-\$ or JP-11307777-\$ or JP-08250742-\$).did. or (JP-2000353811-\$ or US-20030025127-\$ or JP-08250742-\$ or JP-11307777-\$ or JP-05335573-\$).did. | JPO; DERWENT | OR | OFF | 2005/03/06 13:50 |
| S53 | 11 | (JP-2003045892-\$ or JP-2000353811-\$ or JP-05335573-\$ or JP-11307777-\$ or JP-08250742-\$).did. or (JP-2000353811-\$ or US-20030025127-\$ or JP-08250742-\$ or JP-11307777-\$ or JP-05335573-\$).did. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | OFF | 2005/03/06 13:52 |
| S54 | 266 | width near4 gate adj electrode and (overlap overlapping) near6 gate near6 drain | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | OFF | 2005/03/06 13:52 |
| S55 | 144 | width near4 gate adj electrode and (overlap overlapping) near6 gate near6 drain and tft | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/03/06 13:52 |

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| S56 | 47 | width near4 gate adj electrode and (overlap overlapping) near6 gate near6 drain and tft.ti,ab,clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/03/06 13:56 |
| S57 | 7 | width near4 gate adj electrode and (overlap overlapping) near6 gate near6 drain near6 ("mu.m" nm ".ANG.") and tft | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/03/06 13:57 |
| S58 | 2 | jp-05335573\$-\$ did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/16 09:53 |
| S59 | 2 | jp-08250742\$-\$ did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/16 08:41 |
| S60 | 0 | jp-200345892\$-\$ did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/16 08:41 |
| S61 | 2 | jp-2003045892\$-\$ did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/16 08:41 |
| S62 | 346 | gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/16 09:53 |
| S63 | 325 | gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 09:54 |
| S64 | 41 | gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. and polysilicon adj tft | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 09:55 |
| S65 | 7 | gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. and polysilicon adj tft.ti. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 10:19 |

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| S66 | 0 | gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. and polysilicon adj tft.ti. and polysilicon adj tft near4 polysilicon near4 gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 09:56 |
| S67 | 0 | gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. and polysilicon adj tft.ti. and polysilicon adj tft near10 polysilicon near10 gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 09:56 |
| S68 | 0 | gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. and polysilicon adj tft.ti. and polysilicon adj tft same polysilicon near10 gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 09:56 |
| S69 | 2 | jp-2000058849\$\$.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 10:22 |
| S70 | 2 | jp-11307777\$\$.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 10:28 |
| S71 | 2 | jp-2003017502\$\$.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 14:14 |
| S72 | 2 | "20020195604".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 10:29 |
| S73 | 8649 | ((257/59) or (257/72) or (257/270) or (257/346) or (257/351) or (257/355) or (257/356) or (257/387) or (257/390) or (257/391) or (257/392) or (257/393) or (257/394) or (257/395)).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/16 12:40 |
| S74 | 1420 | S73 and (third three) near4 gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/16 12:40 |

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| S75 | 657 | S73 and (third three) near4 gate and (tft otft thin adj film adj transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 12:41 |
| S76 | 2 | (gate adj stack gate-stack) and (thin adj film adj transistor tft otft) and 257/270:ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 14:16 |
| S77 | 182 | (gate adj stack gate-stack) and (thin adj film adj transistor tft otft)"ti,ab,clm." | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 14:17 |
| S78 | 8 | (gate adj stack gate-stack) and (thin adj film adj transistor tft otft).ti,ab,clm. and (overlap overlaps overlapping overlapped) and (self-aligned self-alignment self-align) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 14:19 |
| S79 | 0 | (gate adj stack gate-stack) and (thin adj film adj transistor tft otft).ti,ab,clm. and (overlap overlaps overlapping overlapped) and (self-aligned self-alignment self-align) and low-voltage and high-voltage | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 14:19 |
| S80 | 6 | (gate adj stack gate-stack) and (thin adj film adj transistor tft otft).ti,ab,clm. and (overlap overlaps overlapping overlapped) and (self-aligned self-alignment self-align) and ("low" adj voltage "lower" adj voltage low-voltage and "higher" adj voltage "high" adj voltage high-voltage) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 14:20 |
| S81 | 2 | jp-05335573\$-.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/16 14:27 |
| S82 | 2 | ("5396084").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/16 14:42 |
| S83 | 127 | mondt.xa. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/16 14:47 |

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| S84 | 462 | (tft otft thin adj film adj transistor).ti,ab,clm. and (self-align\$2 self-alignment selfalign\$2 selfalignment) and ((voltage near4 ("high" "higher")) high-voltage) and ((voltage near4 ("low" "lower")) low-voltage) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/16 14:58 |
| S85 | 440 | (tft otft thin adj film adj transistor).ti,ab,clm. and (self-align\$2 self-alignment selfalign\$2 selfalignment) and ((voltage near4 ("high" "higher")) high-voltage) and ((voltage near4 ("low" "lower")) low-voltage) and (thick thickness thicker) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/16 14:59 |
| S86 | 307 | (tft otft thin adj film adj transistor).ti,ab,clm. and (self-align\$2 self-alignment selfalign\$2 selfalignment) and ((voltage near4 ("high" "higher")) high-voltage) and ((voltage near4 ("low" "lower")) low-voltage) and (thick thickness thicker) near6 gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/16 14:59 |
| S87 | 278 | (tft otft thin adj film adj transistor).ti,ab,clm. and (self-align\$2 self-alignment selfalign\$2 selfalignment) and ((voltage near4 ("high" "higher")) high-voltage) and ((voltage near4 ("low" "lower")) low-voltage) and (thick thickness thicker) near6 gate near6 (insulation insulating oxide) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/16 15:00 |
| S88 | 0 | (additional second third separate) near4 gate.clm. and (low-voltage ("lower" "low") near2 voltage)). clm. and (high-voltage ("higher" "high") near2 voltage)).clm. and (thin adj film near2 transistor tft otft).clm. and (overlap overlapped overlaps overlapping).clm. and (self-align self-alignment self-aligned self-aligning).clm. and (thick thickness thicker).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 16:36 |
| S89 | 2 | jp-2000058849\$.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 17:10 |

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| S90 | 2 | jp-11307777\$-.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 17:08 |
| S91 | 2 | jp-2003017502\$-.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 16:37 |
| S92 | 2 | "20020195604".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 17:10 |
| S93 | 8 | S89 S90 S91 S92 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/16 16:37 |
| S94 | 2 | ("20030025127").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/16 16:59 |
| S95 | 2 | jp-2003017502\$-.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/17 11:56 |